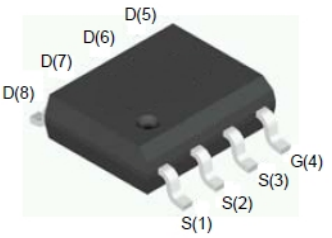
RU60E5H

N-Channel Advanced Power MOSFET

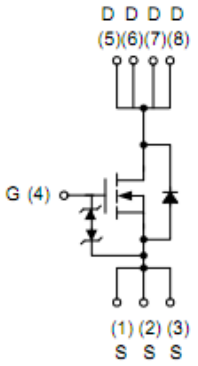
Features

- 60V/5A,
  $R_{DS(ON)}$ =60mΩ (Typ.) @ V_{GS}=10V
  $R_{DS(ON)}$ =70mΩ (Typ.) @ V_{GS}=4.5V
- Super High Dense Cell Design
- Reliable and Rugged
- ESD Protected
- Lead Free and Green Available

Pin Description



SOP-8



N-Channel MOSFET

Applications

- Power Management
- Switch Applications

Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T_A=25°C Unless Otherwise Noted)				
V_{DSS}	Drain-Source Voltage		60	V
V_{GSS}	Gate-Source Voltage		±20	
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	°C
I_S	Diode Continuous Forward Current	T_A=25°C	3	A
Mounted on Large Heat Sink				
I_{DP}	300μs Pulse Drain Current Tested	T_A=25°C	20①	A
I_D	Continuous Drain Current(V_{GS}=10V)	T_A=25°C	5	A
		T_A=70°C	3.7	
P_D	Maximum Power Dissipation	T_A=25°C	2.5	W
		T_A=70°C	1.6	
$R_{\theta JA}$②	Thermal Resistance-Junction to Ambient		50	°C/W

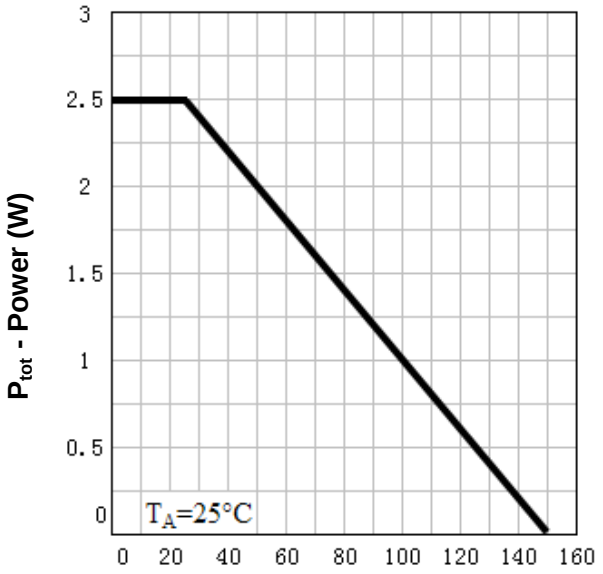
Electrical Characteristics (T_A=25°C Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU60E5H			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=250μA	60			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= 60V, V_{GS}=0V			1	μA
		T_J=85°C			30	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250μA	1.5	2	2.7	V
I_{GSS}	Gate Leakage Current	V_{GS}=±16V, V_{DS}=0V			±10	μA
$R_{DS(ON)}$ ③	Drain-Source On-state Resistance	V_{GS}= 10V, I_{DS}=5A		60	70	mΩ
		V_{GS}= 4.5V, I_{DS}=3.5A		70	80	mΩ
Diode Characteristics						
V_{SD} ③	Diode Forward Voltage	I_{SD}=2.5A, V_{GS}=0V			1.2	V
t_{rr}	Reverse Recovery Time	I_{SD}=2.5A, dI_{SD}/dt=100A/μs		41		ns
Q_{rr}	Reverse Recovery Charge			71		nC
Dynamic Characteristics ④						
R_G	Gate Resistance	V_{GS}=0V,V_{DS}=0V,F=1MHz		0.7		Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}= 30V, Frequency=1.0MHz		460		pF
C_{oss}	Output Capacitance			44		
C_{rss}	Reverse Transfer Capacitance			24		
$t_{d(ON)}$	Turn-on Delay Time	V_{DD}=30V, R_L=12Ω, I_{DS}=2.5A, V_{GEN}= 10V, R_G=6Ω		3		ns
t_r	Turn-on Rise Time			4		
$t_{d(OFF)}$	Turn-off Delay Time			12		
t_f	Turn-off Fall Time			5		
Gate Charge Characteristics ④						
Q_g	Total Gate Charge	V_{DS}=48V, V_{GS}= 10V, I_{DS}=2.5A		16	21	nC
Q_{gs}	Gate-Source Charge			3		
Q_{gd}	Gate-Drain Charge			5		

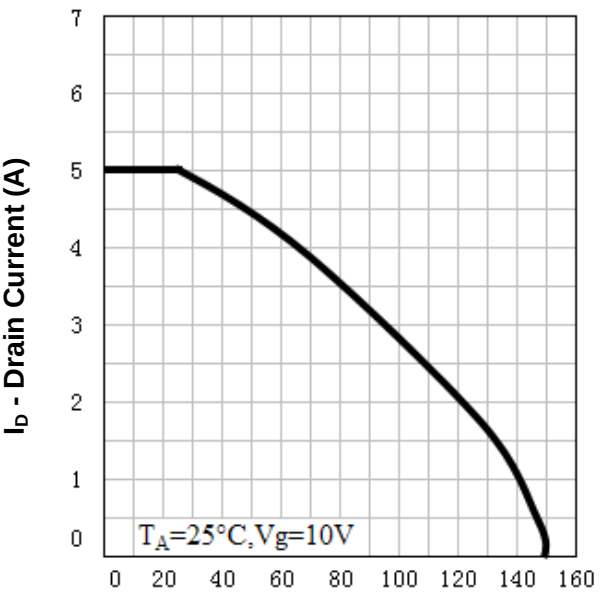
Notes: ①Pulse width limited by safe operating area.
②When mounted on 1 inch square copper board, t ≤10sec.
③Pulse test ; Pulse width≤300μs, duty cycle≤2%.
④Guaranteed by design, not subject to production testing.

Typical Characteristics

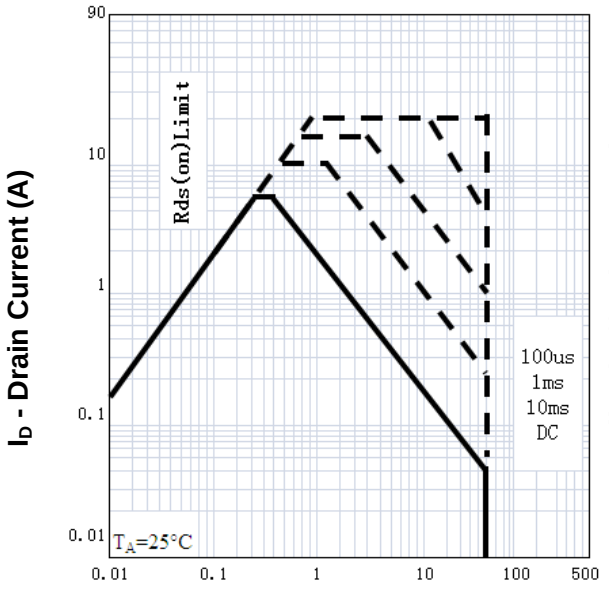
Power Dissipation



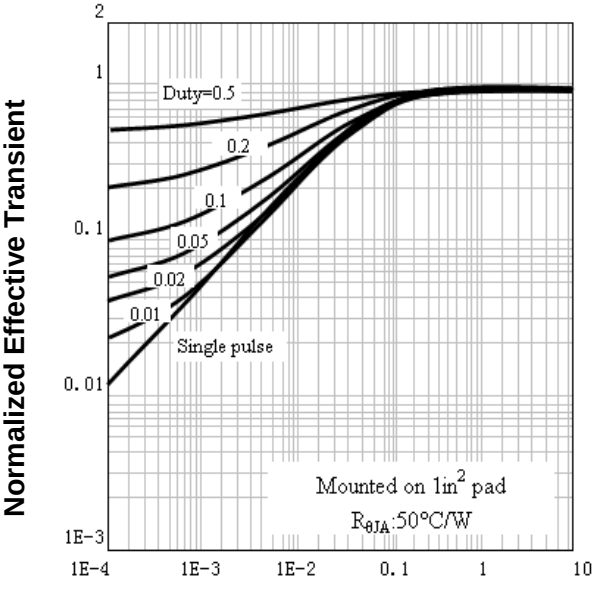
Drain Current



Safe Operation Area

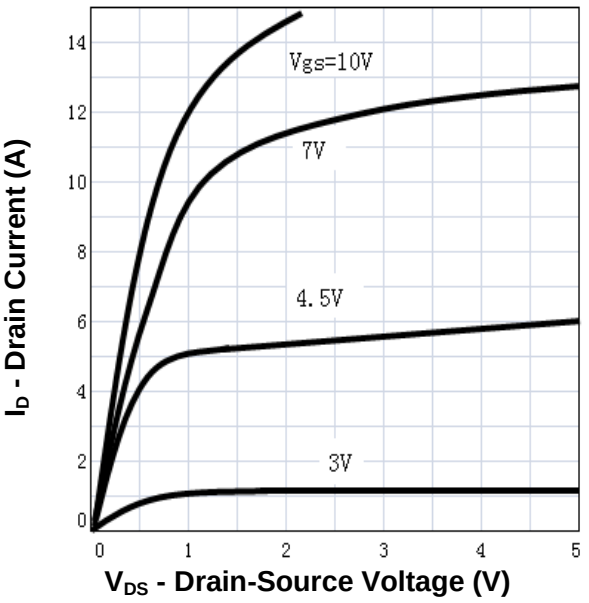


Thermal Transient Impedance

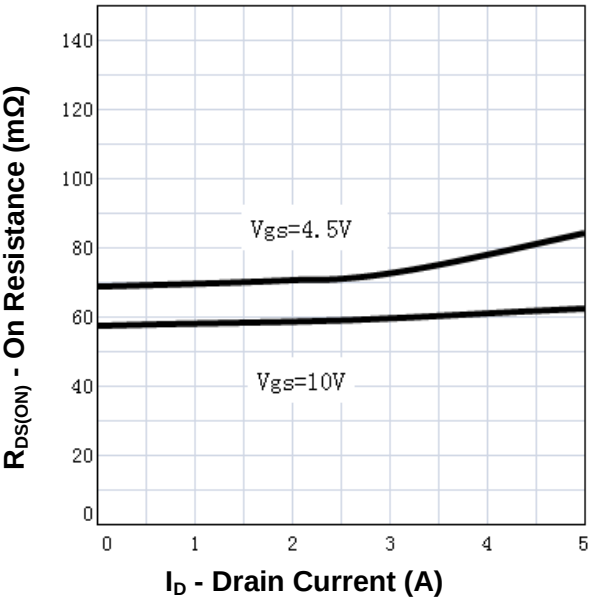


Typical Characteristics

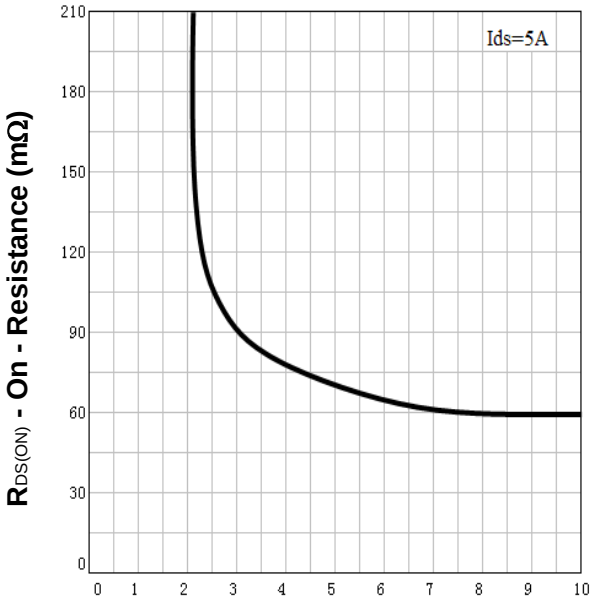
Output Characteristics



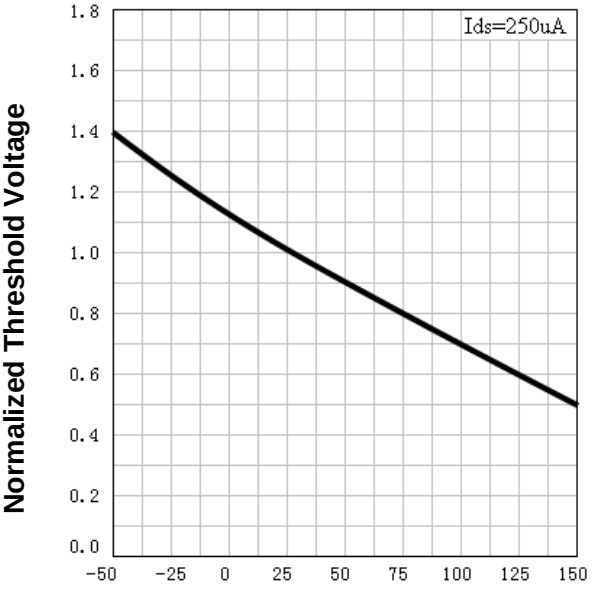
Drain-Source On Resistance



Drain-Source On Resistance

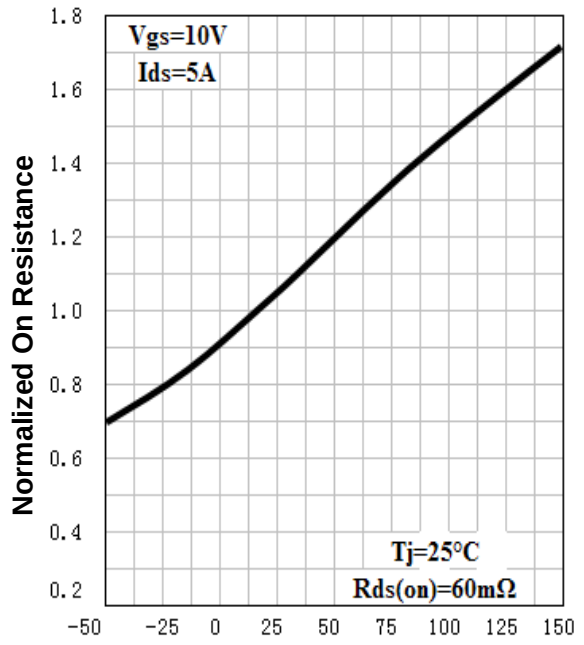


Gate Threshold Voltage



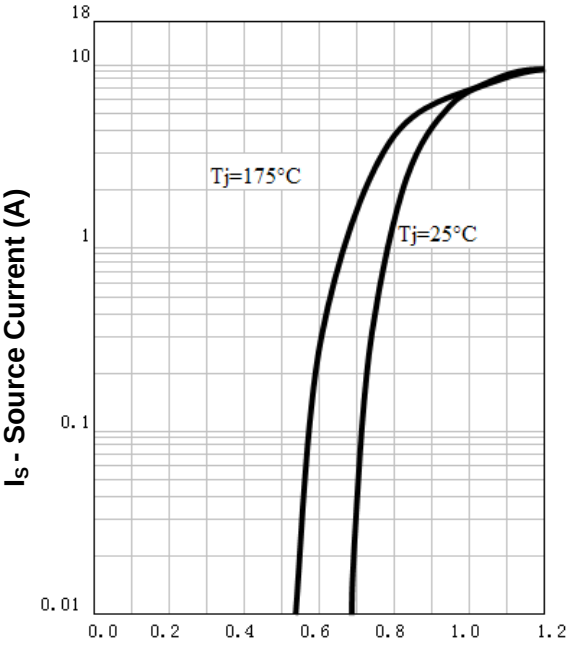
Typical Characteristics

Drain-Source On Resistance



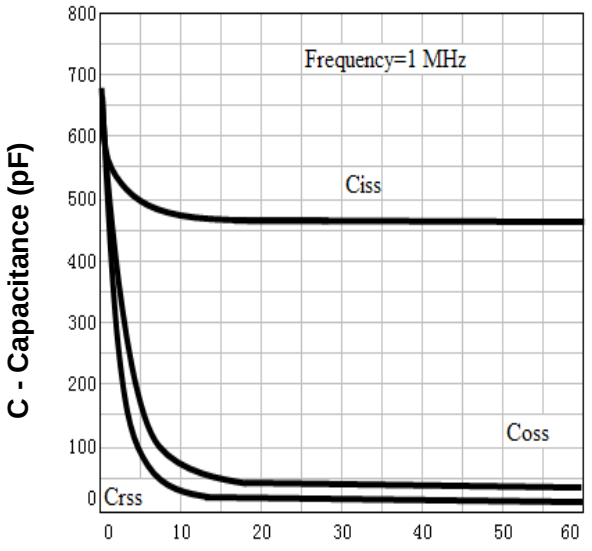
T_j - Junction Temperature (°C)

Source-Drain Diode Forward



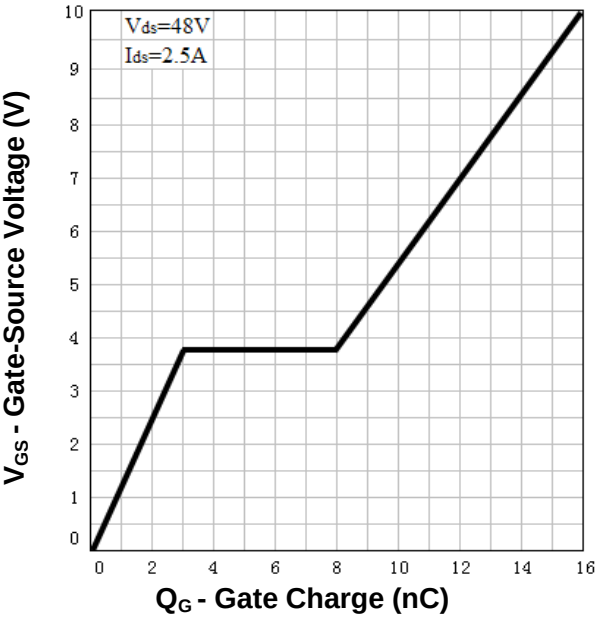
V_{SD} - Source-Drain Voltage (V)

Capacitance



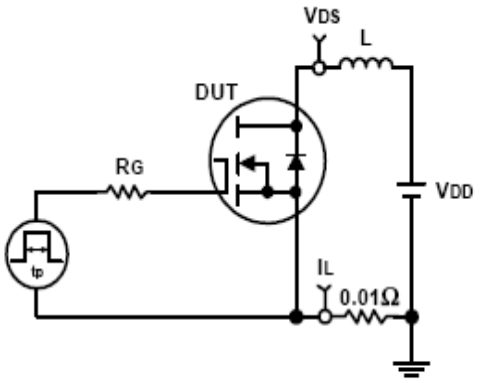
V_{DS} - Drain-Source Voltage (V)

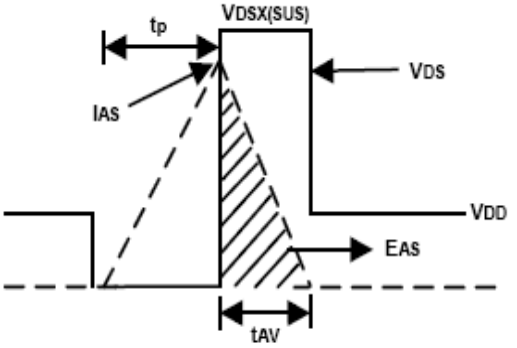
Gate Charge



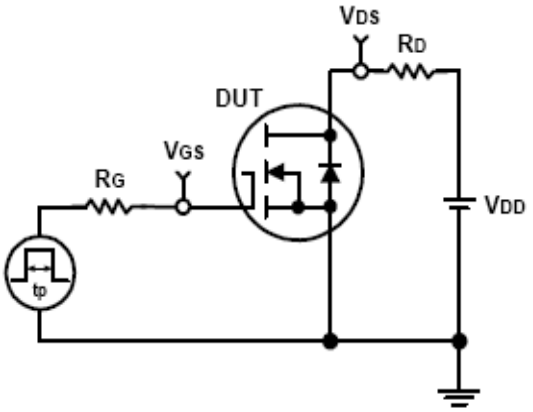
Q_G - Gate Charge (nC)

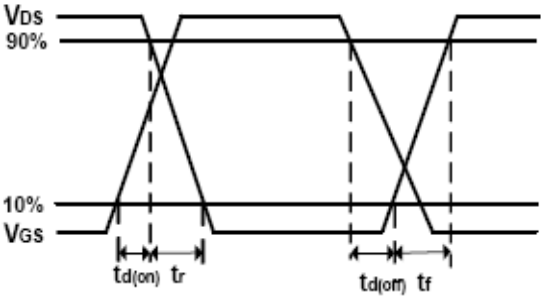
Avalanche Test Circuit and Waveforms





Switching Time Test Circuit and Waveforms



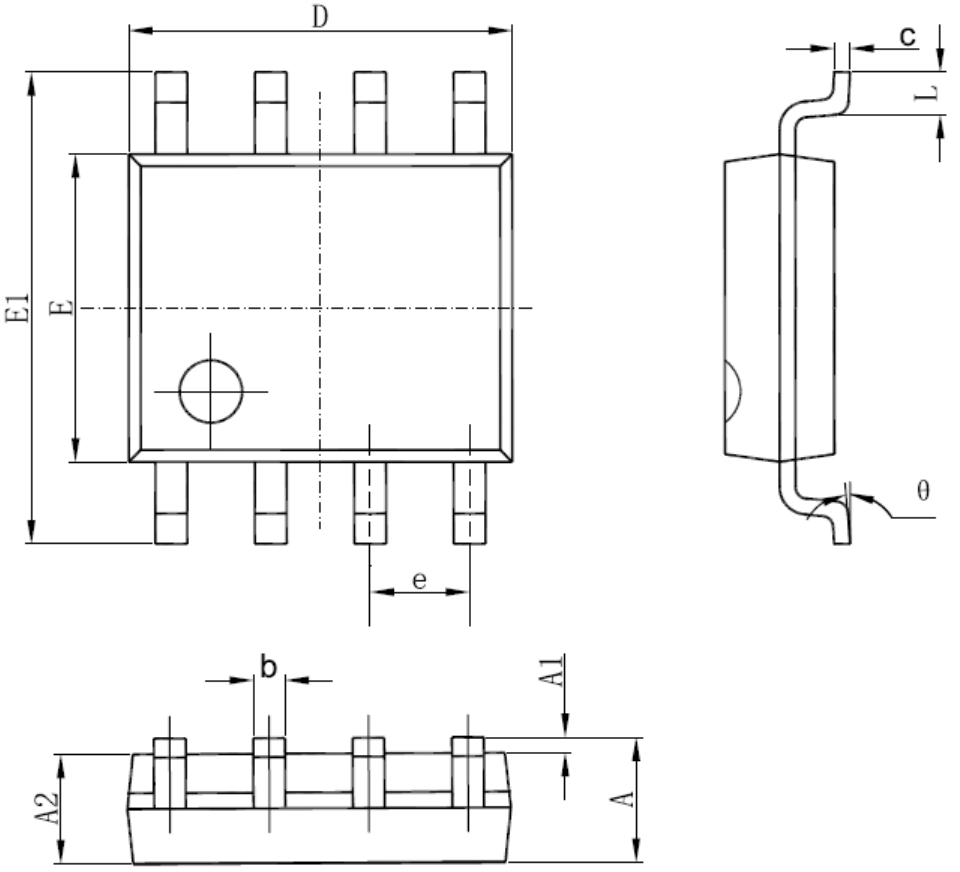


Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU60E5H	RU60E5H	SOP-8	Tape&Reel	2500	13''	12mm

Package Information

SOP-8



SYMBOL	MM		INCH		SYMBOL	MM		INCH	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	1.350	1.750	0.053	0.069	E	3.800	4.000	0.150	0.157
A1	0.100	0.250	0.004	0.010	E1	5.800	6.200	0.228	0.244
A2	1.350	1.550	0.053	0.061	e	1.270 (BSC)		0.050 (BSC)	
b	0.330	0.510	0.013	0.020	L	0.400	1.270	0.016	0.050
c	0.170	0.250	0.006	0.010	θ	0°	8°	0°	8°
D	4.700	5.100	0.185	0.200					

ALL DIMENSIONS REFER TO JEDEC STANDARD
DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS

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